	Application No.	Applicant(s)
A	09/893,188	SINGH ET AL.
Notice of Allowability	Examiner	Art Unit
	Lynette T. Umez-Eronini	1765
The MAILING DATE of this communication appe All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this ap or other appropriate communication GHTS. This application is subject t	plication. If not included
1. This communication is responsive to 4/21/2006.		
2. The allowed claim(s) is/are <u>1-18</u> .		
 3. ☐ Acknowledgment is made of a claim for foreign priority uner a) ☐ All b) ☐ Some* c) ☐ None of the: 1. ☐ Certified copies of the priority documents have 		
2. Certified copies of the priority documents have been received in Application No		
3. Copies of the certified copies of the priority documents have been received in this national stage application from the		
International Bureau (PCT Rule 17.2(a)).		
* Certified copies not received:		
Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application. THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		
4. A SUBSTITUTE OATH OR DECLARATION must be submi INFORMAL PATENT APPLICATION (PTO-152) which give	itted. Note the attached EXAMINER es reason(s) why the oath or declara	'S AMENDMENT or NOTICE OF ation is deficient.
5. CORRECTED DRAWINGS (as "replacement sheets") mus	t be submitted.	
(a) ☐ including changes required by the Notice of Draftsperso		948) attached
1) hereto or 2) to Paper No./Mail Date		,
(b) ☐ including changes required by the attached Examiner's Paper No./Mail Date	Amendment / Comment or in the C	Office action of
Identifying indicia such as the application number (see 37 CFR 1. each sheet. Replacement sheet(s) should be labeled as such in the	84(c)) should be written on the drawine header according to 37 CFR 1.121(ngs in the front (not the back) of d).
 DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL. 		
Attachment(s)	_	
1. Notice of References Cited (PTO-892)		atent Application (PTO-152)
2. Notice of Draftperson's Patent Drawing Review (PTO-948)	6. ☐ Interview Summary Paper No./Mail Dat	(PTO-413), te
3. Information Disclosure Statements (PTO-1449 or PTO/SB/08 Paper No./Mail Date	Paper No./Mail Dat B), 7. ☐ Examiner's Amendr	nent/Comment
4. Examiner's Comment Regarding Requirement for Deposit of Biological Material	8. Examiner's Stateme	ent of Reasons for Allowance
or biological material	9. Other	

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DETAILED ACTION

REASON FOR ALLOWANCE

- 1. Claims 1-18 are allowed.
- 2. The following is an examiner's statement of reasons for allowance:

Applicants' Remarks (pages 47-13) in Amendment filed 4/21/2006 were persuasive in showing the formerly applied references failed to teach a method of forming a dual damascene by simultaneously etching a first and a second patterned photoresist through an insulation layer, in a single etch process to form an image of the first and second patterned photoresist in the insulation layer.

As to claims 1-8, the prior art of record taken alone or in combination fails to suggest, teach or render obvious a method for making a dual damascene pattern in a single etch process, which comprises: simultaneously etching an insulative layer through a first patterned photoresist layer that has been cured and through a second patterned photoresist layer, wherein the an image of the first and second patterned photoresist are formed in the insulative layer, in combination with the rest of the limitations of the claims.;

As to claims 9-14, the prior art of record taken alone or in combination fails to suggest, teach or render obvious a method for making a dual damascene pattern in a single etch process, which comprises: simultaneously etching an insulative layer through a first patterned photoresist layer that has been irradiated with UV light and through a second patterned photoresist layer, wherein the an image of the first and

second patterned photoresist are formed in the insulative layer, in combination with the rest of the limitations of the claims; and

As to claims 15-18, the prior art of record taken alone or in combination fails to suggest, teach or render obvious a method for making a dual damascene pattern in a single etch process, which comprises: simultaneously etching an insulative layer through a patterned positive photoresist layer and through a negative photoresist layer, wherein an image of the first and second photoresist are formed in the insulative layer, in combination with the rest of the limitations of the claims.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Lynette T. Umez-Eronini whose telephone number is 571-272-1470. The examiner is normally unavailable on the First Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton can be reached on 571-272-1465. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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May 3, 2006